

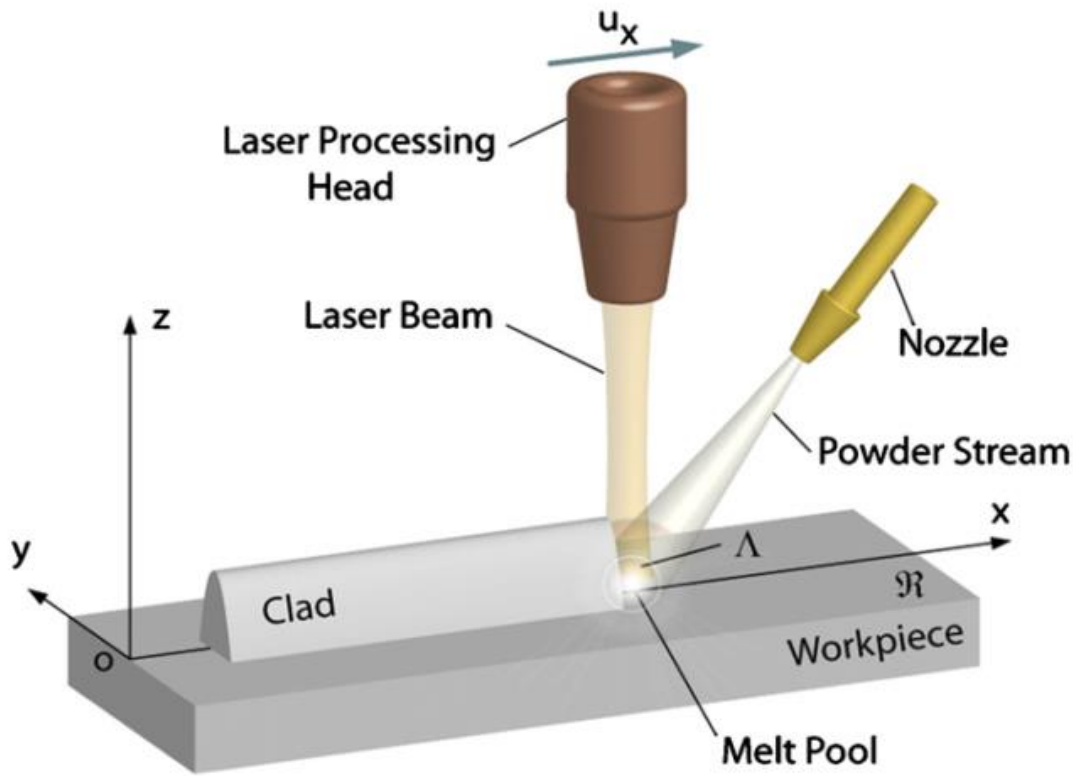
Séminaire 13 Decembre 2021

About the use of Phase Field and FE  
to predict microstructures,  
*Application on AlSi10Mg samples produced  
by Additive Manufacturing*

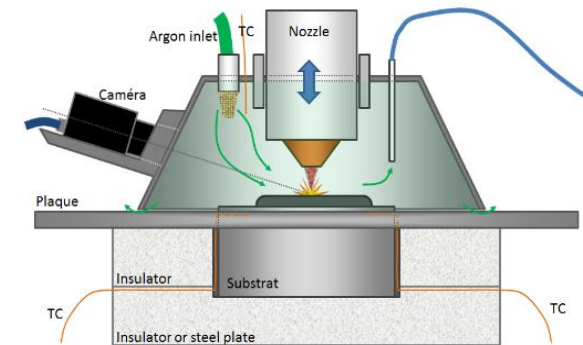
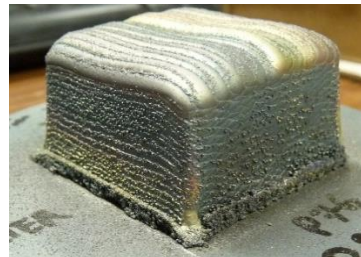
S. Fetni, J. Delahaye, A. Mertens, A.M. Habraken



# Laser cladding or Directed Energy Deposition DED



High temperature gradient  
Complex cyclic temperature history



Directed Energy Deposition

Studied Variant:  
Powder stream and laser beam are confocal  
High power > 1000W  
Thick layer 0.X mm

Heterogeneity of microstructure formed as previous deposit is heated by the laser high energy

# Laser Powder Bed Fusion Process L-PBF (Selective Laser Melting)

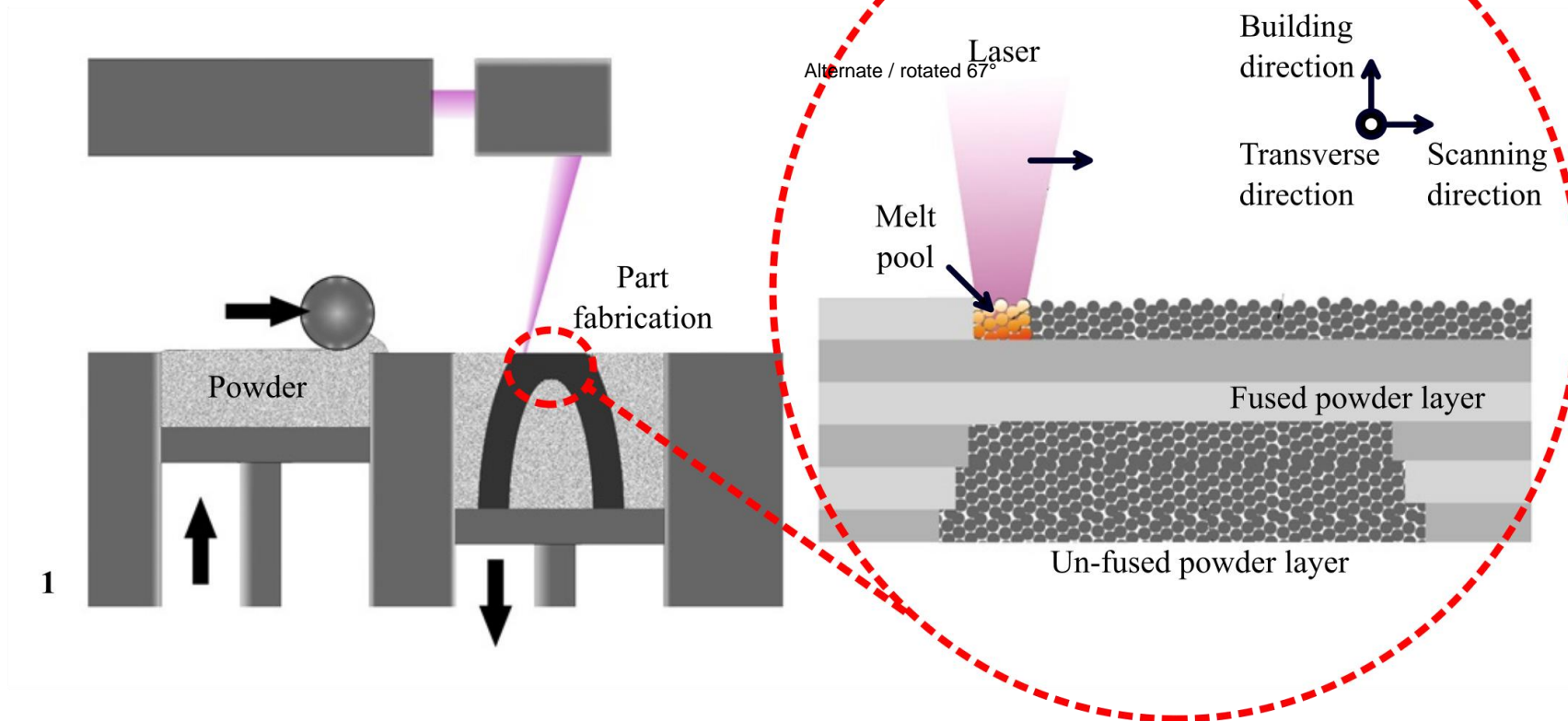
Compared with DED : smaller laser energy

Microstructure heterogeneity formed versus height ↓

Job length can generate heat post treated microstructure

Smaller layer deposition per layer

Still : high temperature gradient  
complex cyclic temperature history



<sup>1</sup>[https://en.wikipedia.org/wiki/Selective\\_laser\\_melting](https://en.wikipedia.org/wiki/Selective_laser_melting)

# Contents

## Background & motivations

- FE model in AM
- AlSi10Mg Microstructure evolution

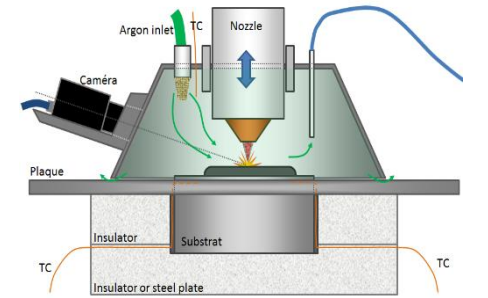
## FE Model of L-PBF AlSi10Mg

## Phase-field model of microstructure evolution:

- Model description
- Model parameters
- Simulated calorimetric curve

## Conclusions

# Accurate thermo-physical properties + double, triple validation(s) of FE results



Directed Energy Deposition

-3D FE models: each Layer-Track modeled (5 mm height)

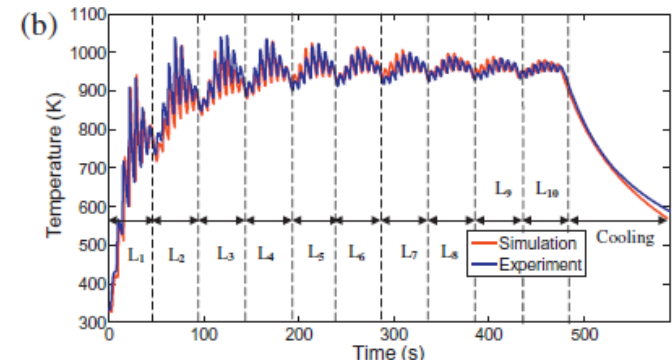
- To adjust laser absorptivity & boundary conditions (convection, radiation), multiplicative factor of liquid conductivity

-Ti<sub>6</sub>Al<sub>4</sub>V alloy: comparison of different laser paths & FE validations

→ measured Tp histories,

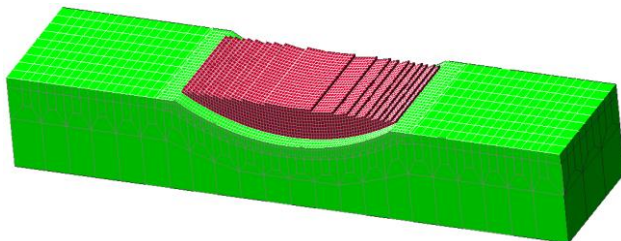
→ hardness map

→ Optical or SEM characterization, phase + melt pool shape

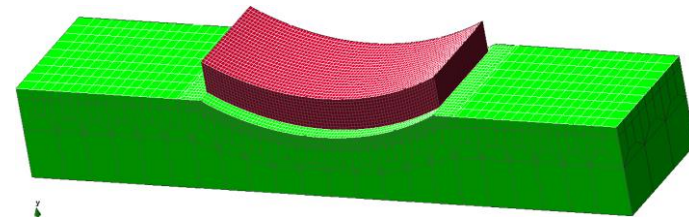


For CTL

Decreased Track Length



Constant Track Length CTL



# Need of accurate thermo-physical properties + double, triple validation of FE results

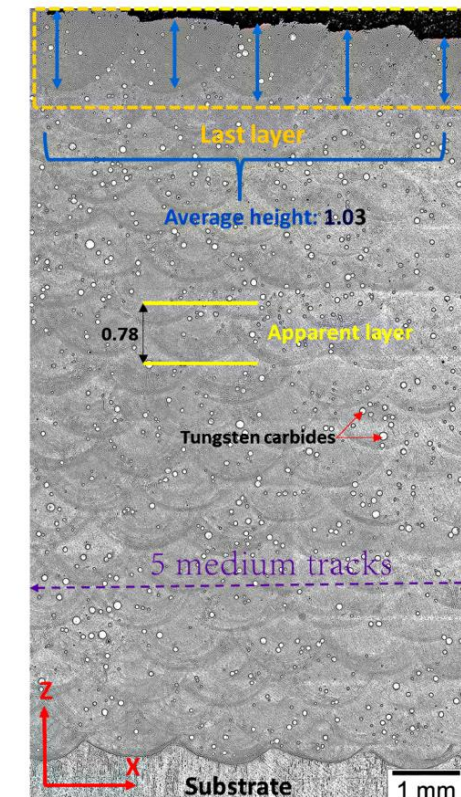
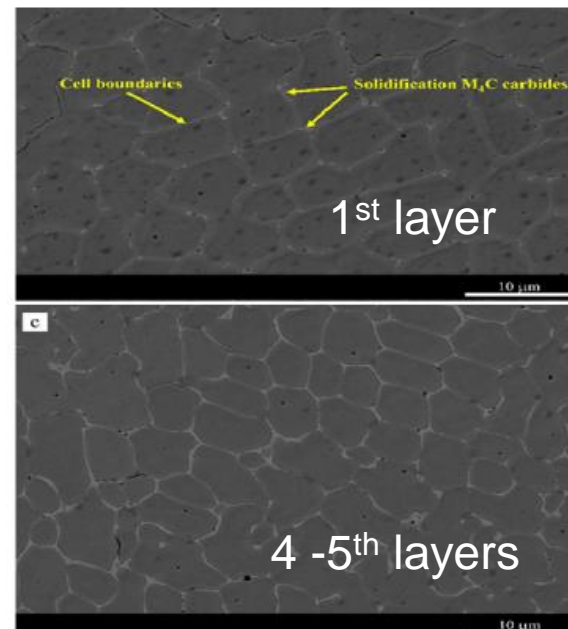
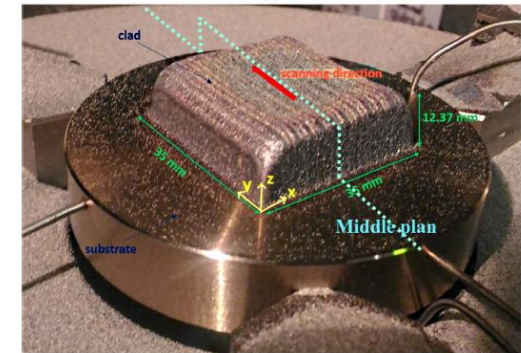
- 2D FE models each layer is modeled to adjust: laser absorptivity (**virtual** factor) & boundary conditions (convection, radiation) & multiplicative factor of liquid conductivity & **virtual iddle time**

**316L + WC:** microstructure understanding & FE validations

- measured Tp histories,
- melt pool size (OM)
- carbide distribution (SEM),
- HAZ (SEM),

S. Fetni Materials & Design (2021), 204(109661)

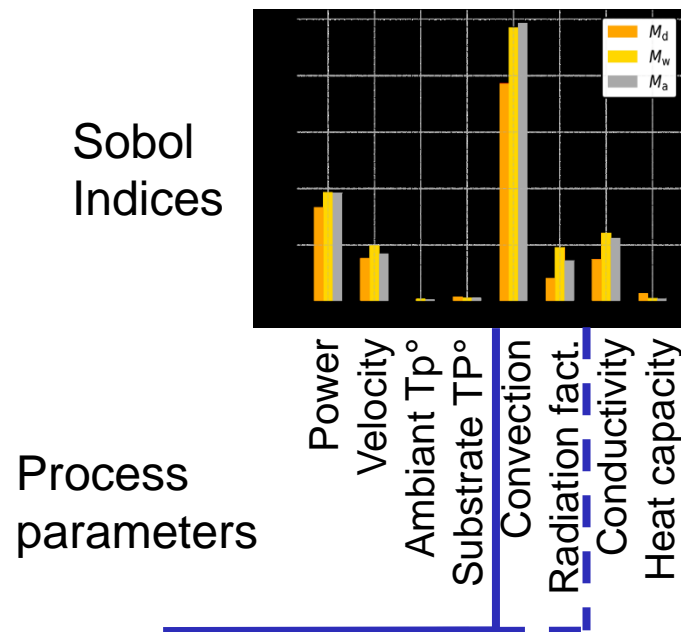
T. Maurizi-Enciri Advanced Engineering Materials (2020) + submitted (2021)



# Need of accurate thermo-physical properties + double, triple validation of FE results

- M4 material (2D or 3D FE models), comparison of bulk or thin wall samples
  - measured Tp history,
  - Optical microscopy: melt pool shape
  - SEM : carbide heterogeneous distribution
- Surrogate model (FFNN FeedForward Neural Network) for uncertainty propagation on melt pool depth, width, area for bulk samples

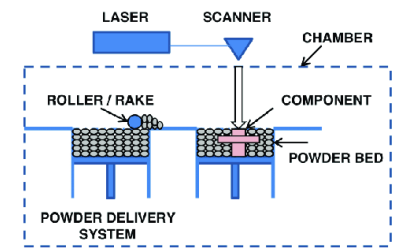
M4 = high speed steel



Monte Carlo simulation  
FE 25 days... // FFNN 3h30

R. Jardin 2019 Materials Letters, 2020 Metals  
T.Q.D. Pham 2021 J. of Intelligent Manufacturing  
T.Q.D. Pham Submitted Probabilistic Eng. Mechanics

According *J. Manuf. Sci. Eng.* Apr 2019,  
141(4): 040801 conductivity affects L-PBF  
part quality too....

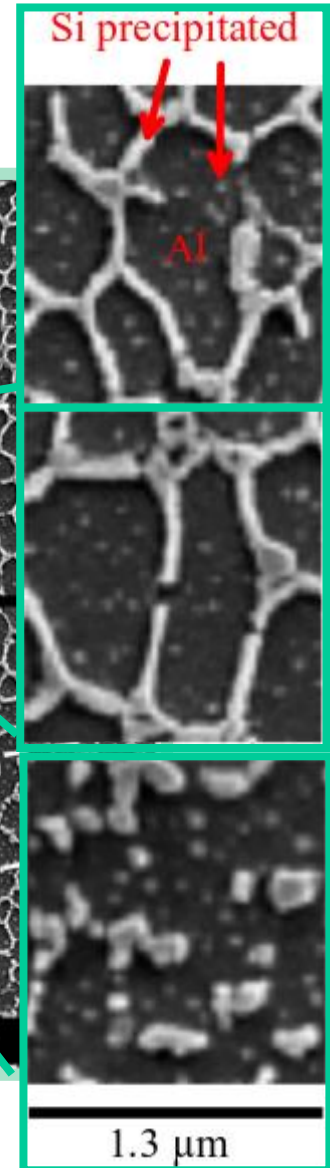
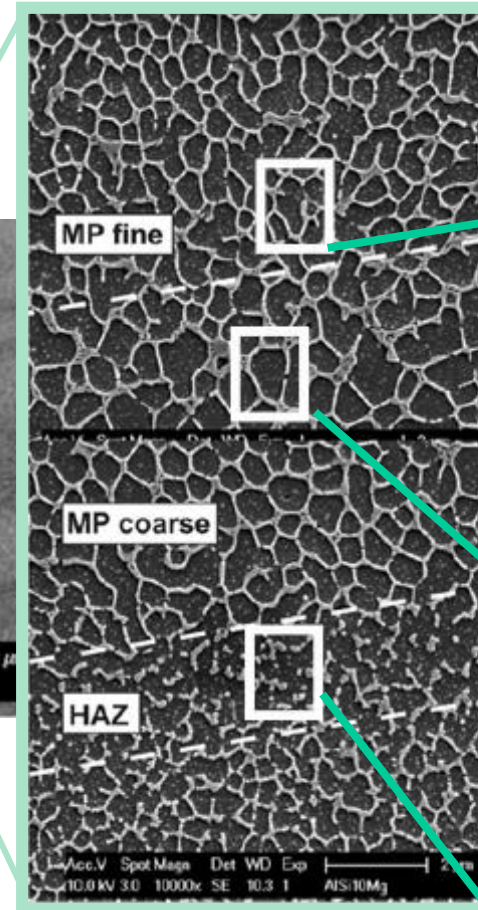
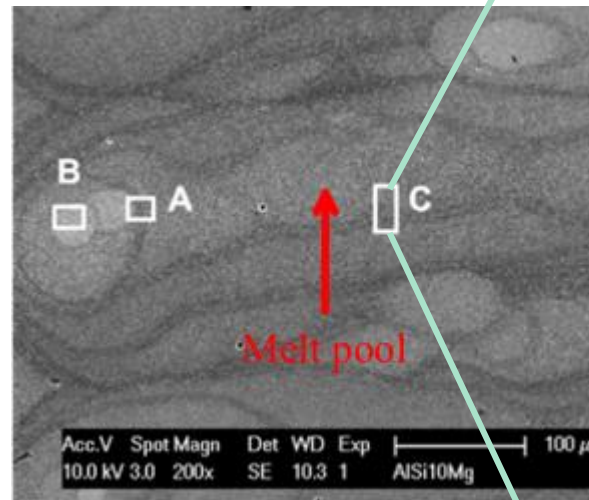


# AISI10Mg Microstructure As Built L-PBF

Melt pool of stable size  
 considering the laser path  
 bar samples, 60  $\mu\text{m}$  thick layer

Melt pool Core  
 = fine cell (MPF)

Melt pool Boundary  
 = coarse cell (MPC)  
 = Heat Affected Zone  
 (HAZ)



## Out of Balance Microstructure



# AlSi10Mg Microstructure As Built L-PBF

## Si atoms

→ Walls (eutectic rich zone Al Si + Si precipitate)

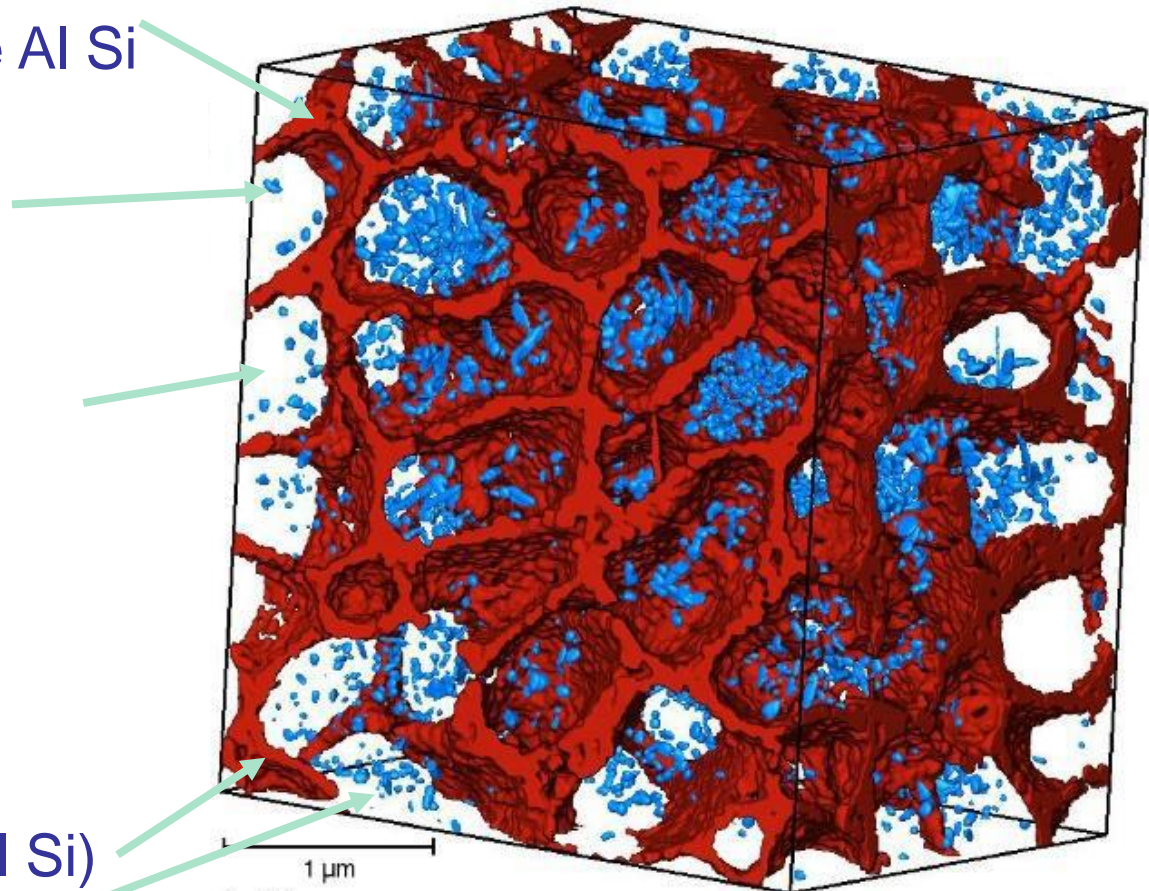
→ Si Precipitate in the cell

→ Si in sursaturated\* solid solution within the cell

## Al atoms

Walls (eutectic rich zone Al Si)

Solid Solution Al Si

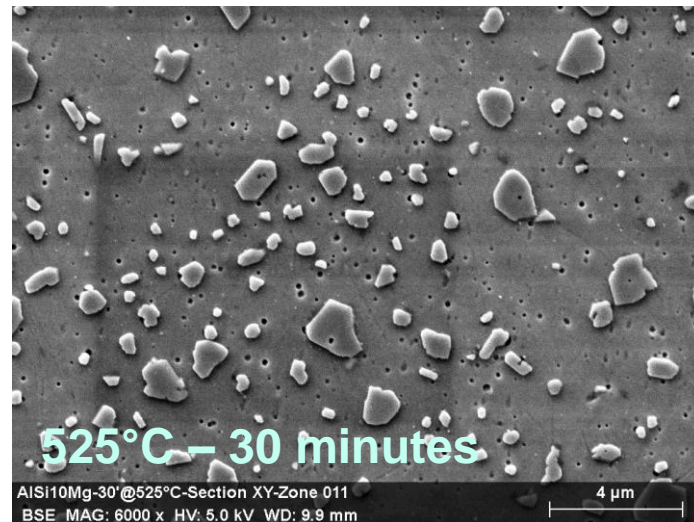
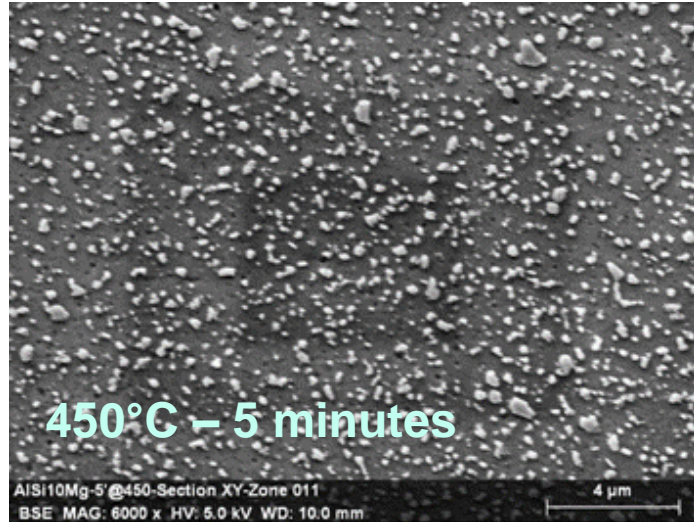


J.G. Santos Macías Acta Materialia 201 (2020)  
L. Zhao Materials Science & Engineering A 764 (2019)

Plate samples, P 390 W, Thickness layer 30μm but still this skeleton microstructure around cells

# AlSi10Mg Microstructure evolution

Thermal treatments applied on As built samples



During L- PBF

in HAZ phase,

“similar” microstructure appears

in Al-Si cells the size of Si precipitates

can varies with process parameters

# Differential scanning calorimetry (DSC) applied on As-Built sample two times “1<sup>st</sup>, 2<sup>nd</sup> run” + dilatometry + Laser-Flash of AlSi10Mg

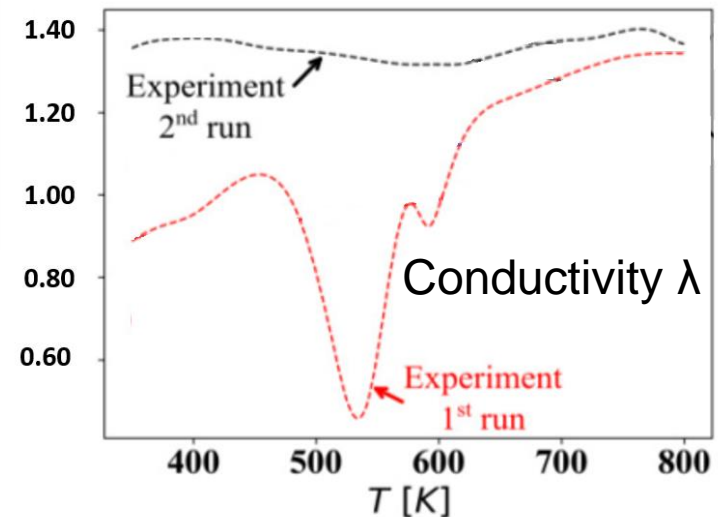
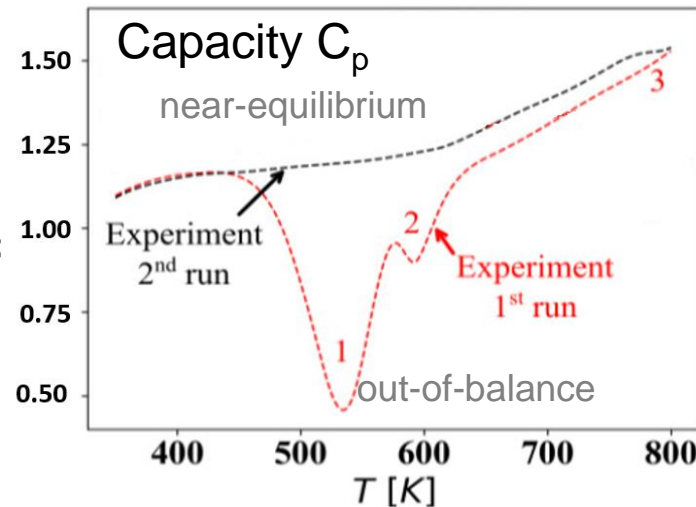
Cooling / Heating rate in DSC: 1.7 K.s<sup>-1</sup>

Direct experimental post treatment

Cooling / Heating rate in L-PBD: 10<sup>6</sup> K.s<sup>-1</sup> What a different range!!!..

## Assumptions\*

1. Si atoms from sur Al-Si saturated solution diffuse to Si precipitates ?
2. Si precipitates growth
3. Walls dissolve ?



## Phase Field

→ microstructure → analytical formula →  $C_p$ ,  $\lambda$

\*Y. Birol Journal of Alloys and Compounds. 439 (2007)

# Conclusion

FE Model of L-PBF of AlSi10Mg

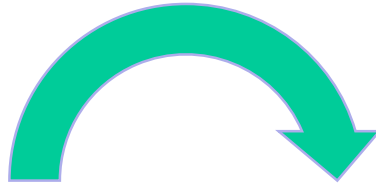
-needs a data set,

-can provide a  $T_p^\circ$  history

Phase-field model of microstructure

-need a  $T_p^\circ$  history,

-could provide data set for FE ?



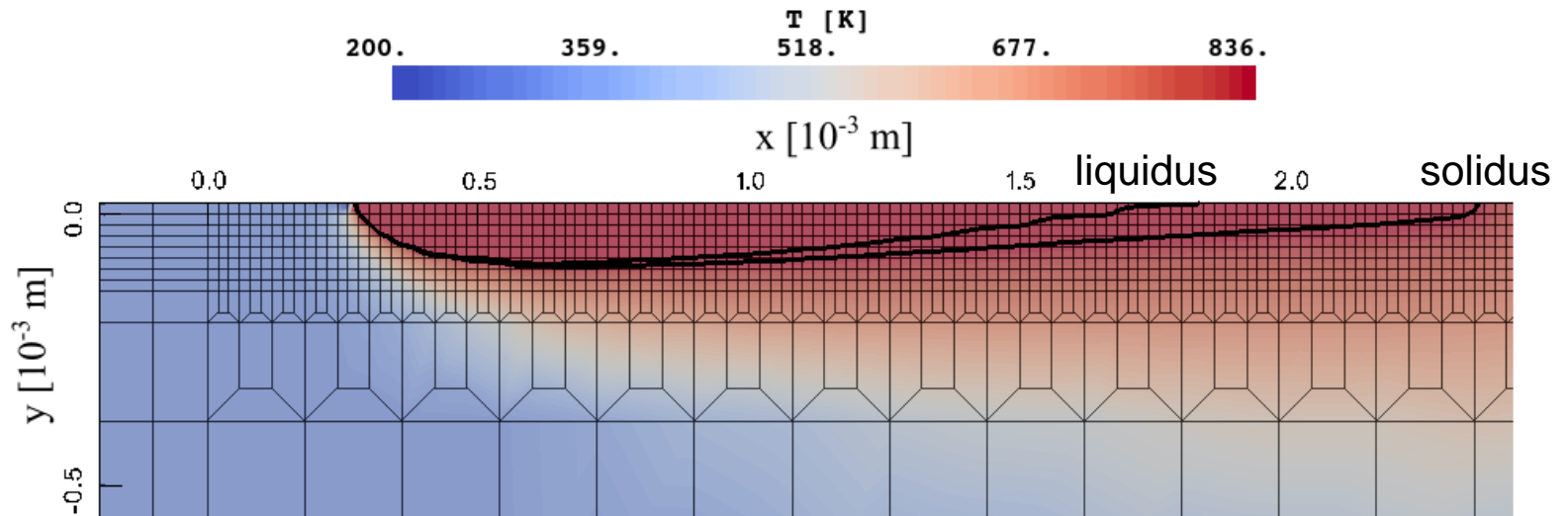
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# FE simulation features

Lagamine non  
linear  
software with  
birth element  
technique



Just a part, mesh is larger (width 3.64 mm and height 3.79 mm)

- the “best” thermo-physical properties data set (next slide)
- & “physical idle” time based on process parameters
- & boundary conditions (convection, radiation) based on literature
- & **tuned** laser absorption coefficient

- the vertical profile of  $tp^\circ$  for different element sizes (10, 20, 40  $\mu\text{m}$ )
- Temperature field is converged, 40  $\mu\text{m}$  is OK

- the case of 5 layers has been studied (remeshing strategy)
- Temperature history between the different layers are stable

→ **Discussion**  
**40  $\mu\text{m}$  element**  
**1 Layer case**

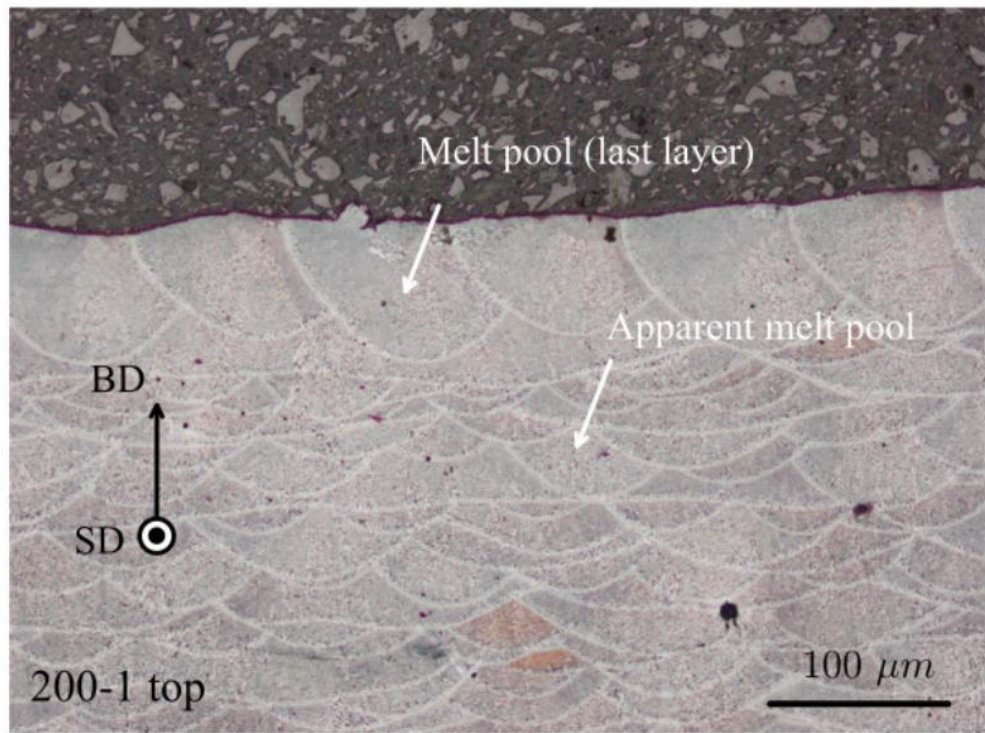
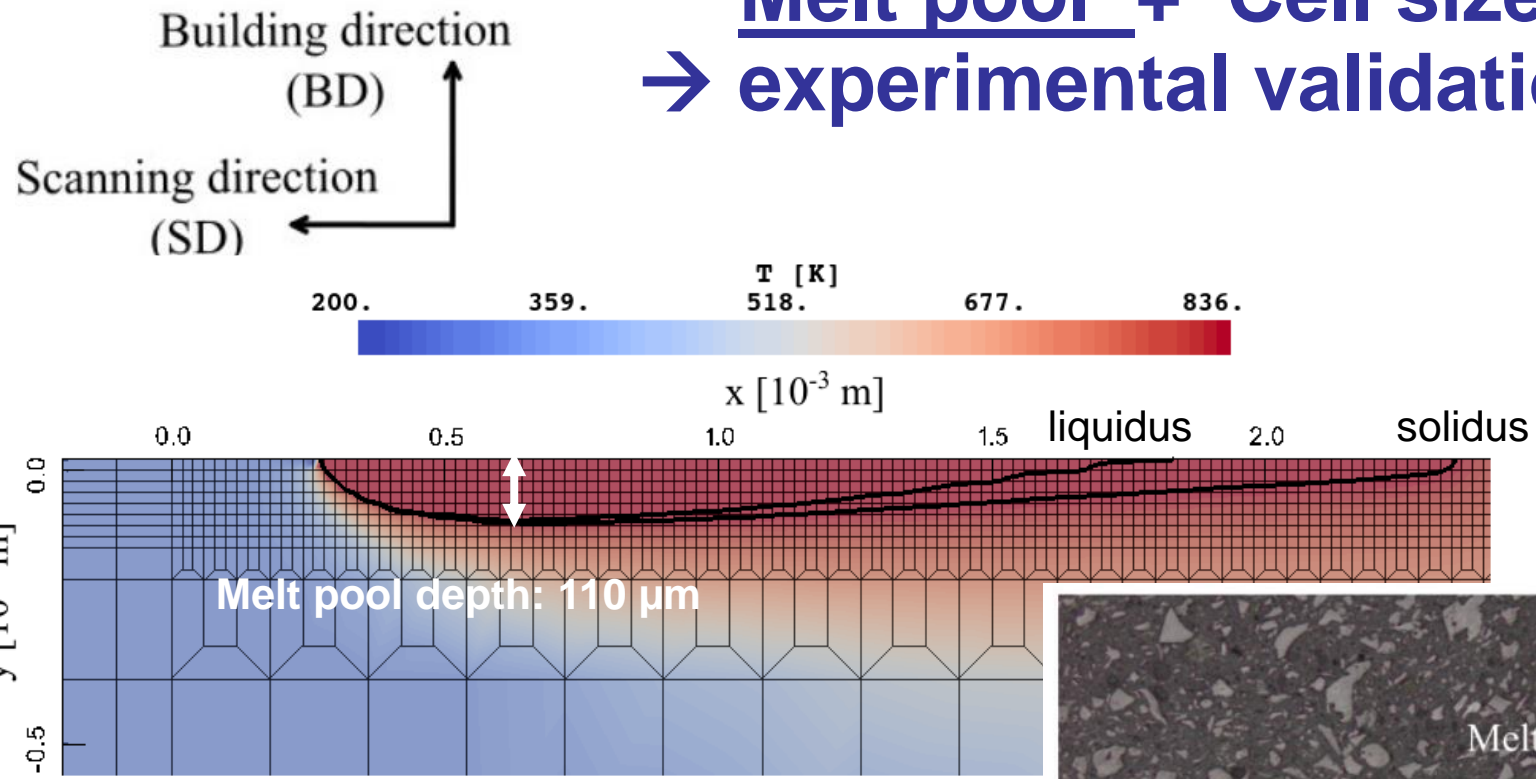
# Thermo Physical data set for FE model

- Analytical model **for the powder**: Zener-Schlunder like model  
(Sih and Barlow 2004 Particul. Sc. Technol. 22.4)
- Rapid solidification model\*\* (Al-Si system) **for mushy state** in L-PBF condition
- CALPHAD (Al-Si system) computation at high  $T_p$ , different improvements tested
- DSC Measurements **for the metastable As built microstructure** in solid state
- Measured value **for the liquid state** with a factor 1 or 2 for taking into account Marangoni effect  
(liquid convection generated by variable surface tension in the melt pool)

\*R. Trivedi Dendritic growth, International Materials Reviews 34:1-39 (2) (1994)

\*\*W. J. BOETTINGER 'Fourth conf. on rapid solidification', 13; 1988, Baton Rouge, LA, Claitor's Publishing Division.

# Melt pool + Cell size → experimental validation

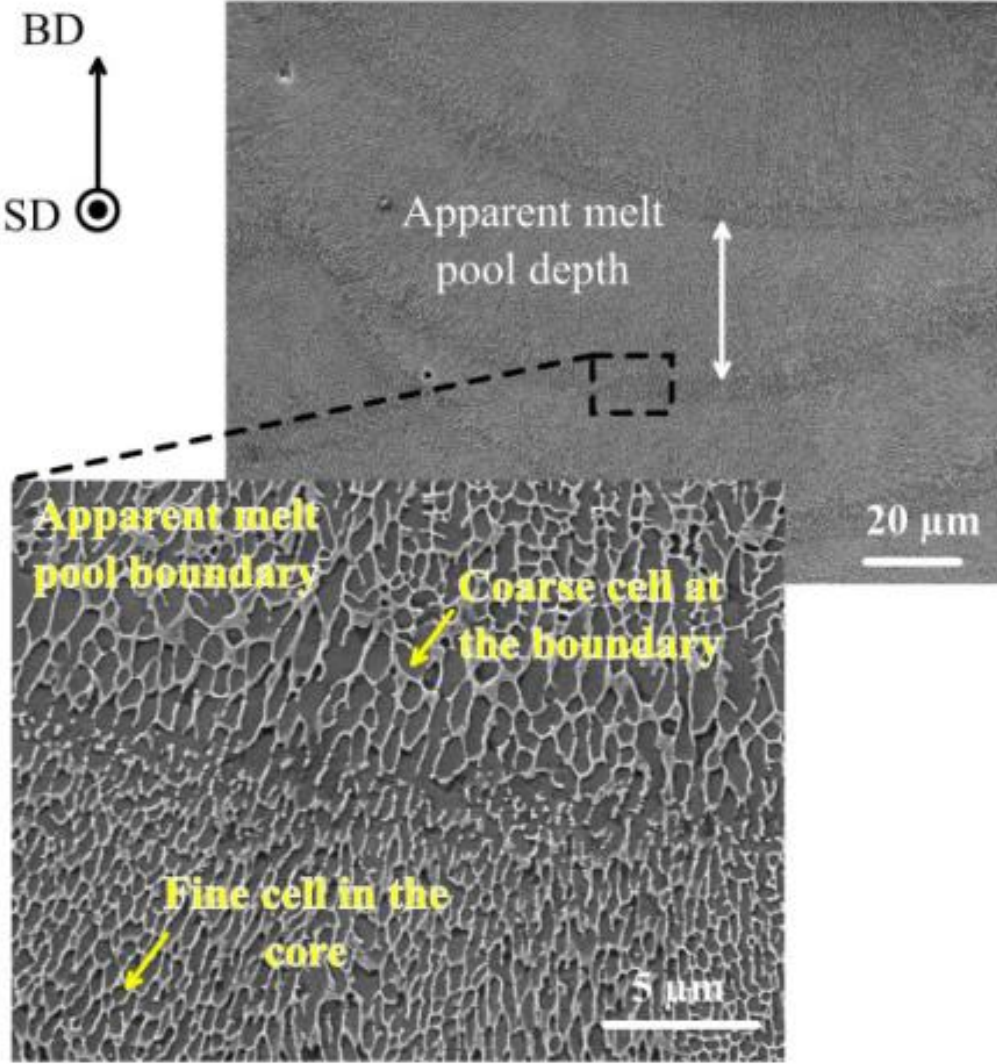
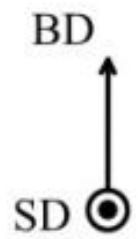
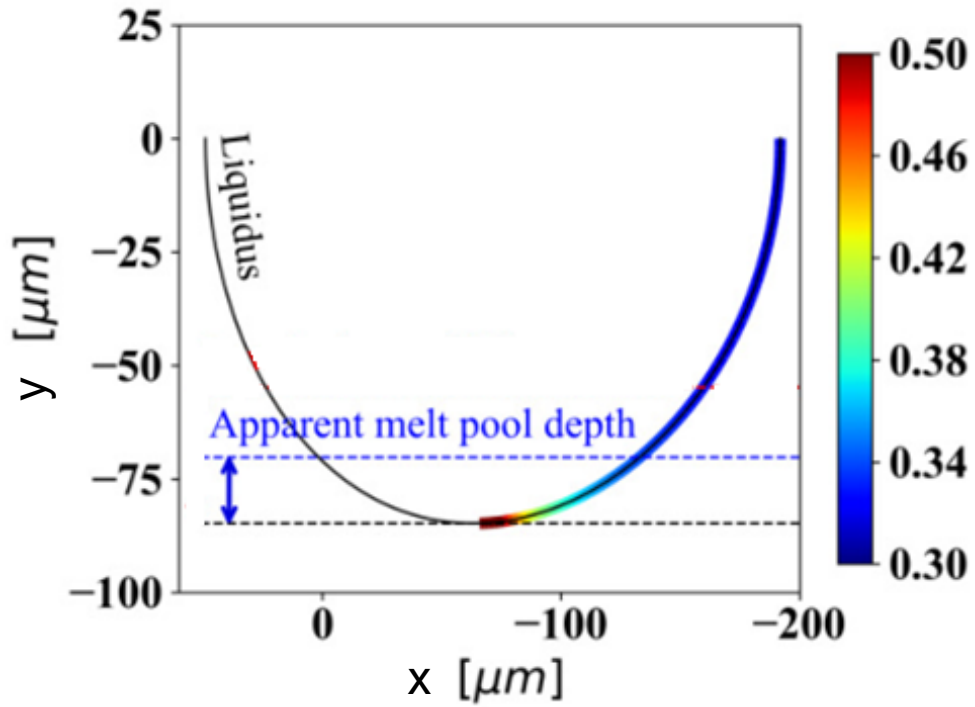
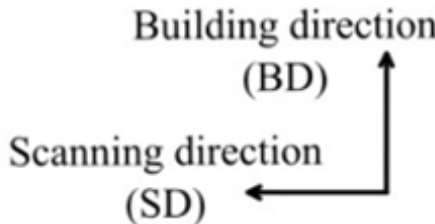




# Melt pool and Cell size → experimental validation

Matyja's\* equation :

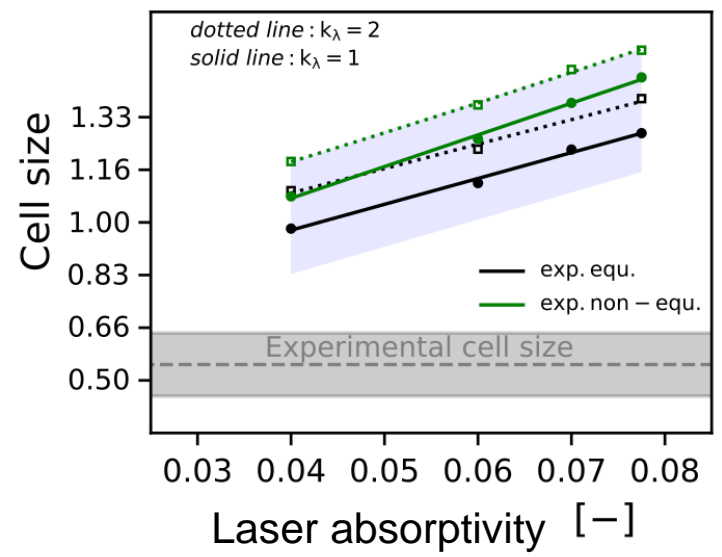
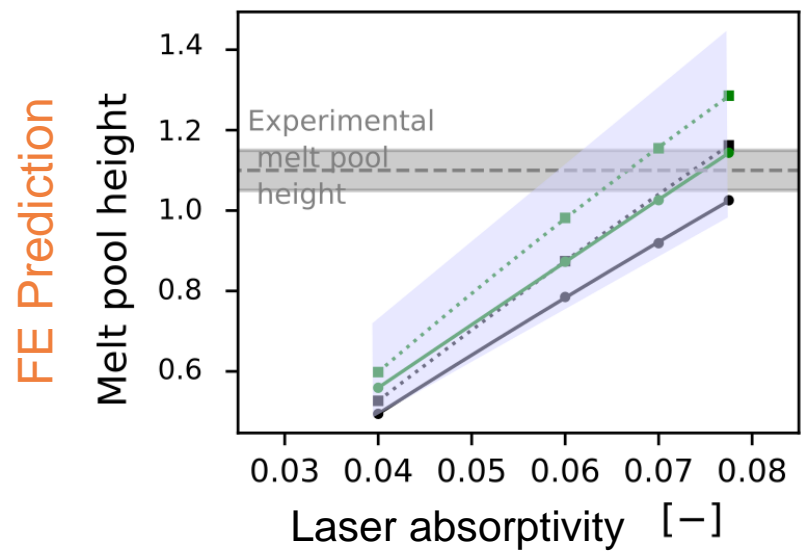
$$L_{cel} = 43.2 \left( \frac{\partial T}{\partial t} \Big|_{T_{liq}} \right)^{-0.324}$$



\* H. Matyja, Journal of the Institute of Metals. 96 (1968) 30–32.

# Tuning laser absorptivity

For fixed convection & radiation coefficient, identified laser absorptivity highly depends on input data



## FE Assumptions

$c_p$  and  $k$

Shaded zone:  
Calphad with  
different  
assumptions

DSC  
experiment

— 1st Run  
— 2nd Run

... Marangoni  
 $k \times 2$

Why ?

- 2D FE assumption
- solid FE model
- Accuracy of material thermo-physical properties

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needs a data set, can provide a  $T_p^\circ$  history
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  - Model parameters
  - Simulated calorimetric curve

## Conclusions

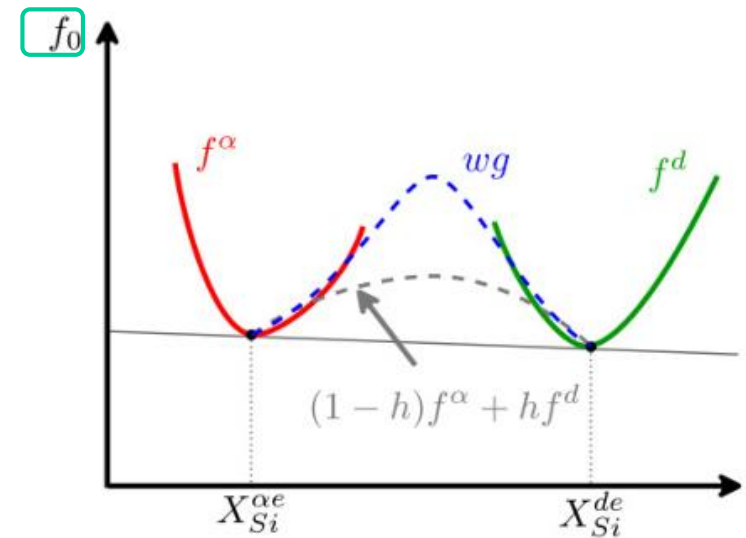
# Phase Field Model

## Free energy formulation

- Kim Kim Suzuki “KKS” model\*
- Interface considered as mixture of both phases with the same chemical potential

Homogeneous free energy density

$\eta=1$  Diamond d Si  
 $=0$  FCC Al  $\alpha$



Non-homogeneous free energy

$$\mathcal{F} = \langle V_m \rangle \int_V \left( f_0(X_{Si}, \eta, T) + \frac{\kappa^2}{2} (\nabla \eta)^2 + e_{el} \right) dV$$

Homogeneous free energy density

e for equilibrium

Molar fraction of Si

Average molar volume

Molar fraction of Si

Phase

Temperature

Interface contribution

Elastic strain energy

Double-well potential function of height w

Interpolation function

Si precipitate

Al matrix

$$f_0(X_{Si}, \eta, T) = \frac{1}{\langle V_m \rangle} [h(\eta) f^d(X_{Si}, T) + (1 - h(\eta)) f^\alpha(X_{Si}, T) + wg(\eta)]$$

\* S.G. Kim Physical Review E 60 (6) (1999) 12 and J.Z. Zhu, Acta Materialia 52 (2004)

# Phase Field Model

Elastic strain energy

$$e_{el} = \frac{1}{2} C_{ijkl} (\epsilon_{ij} - \epsilon_{ij}^0) (\epsilon_{kl} - \epsilon_{kl}^0)$$

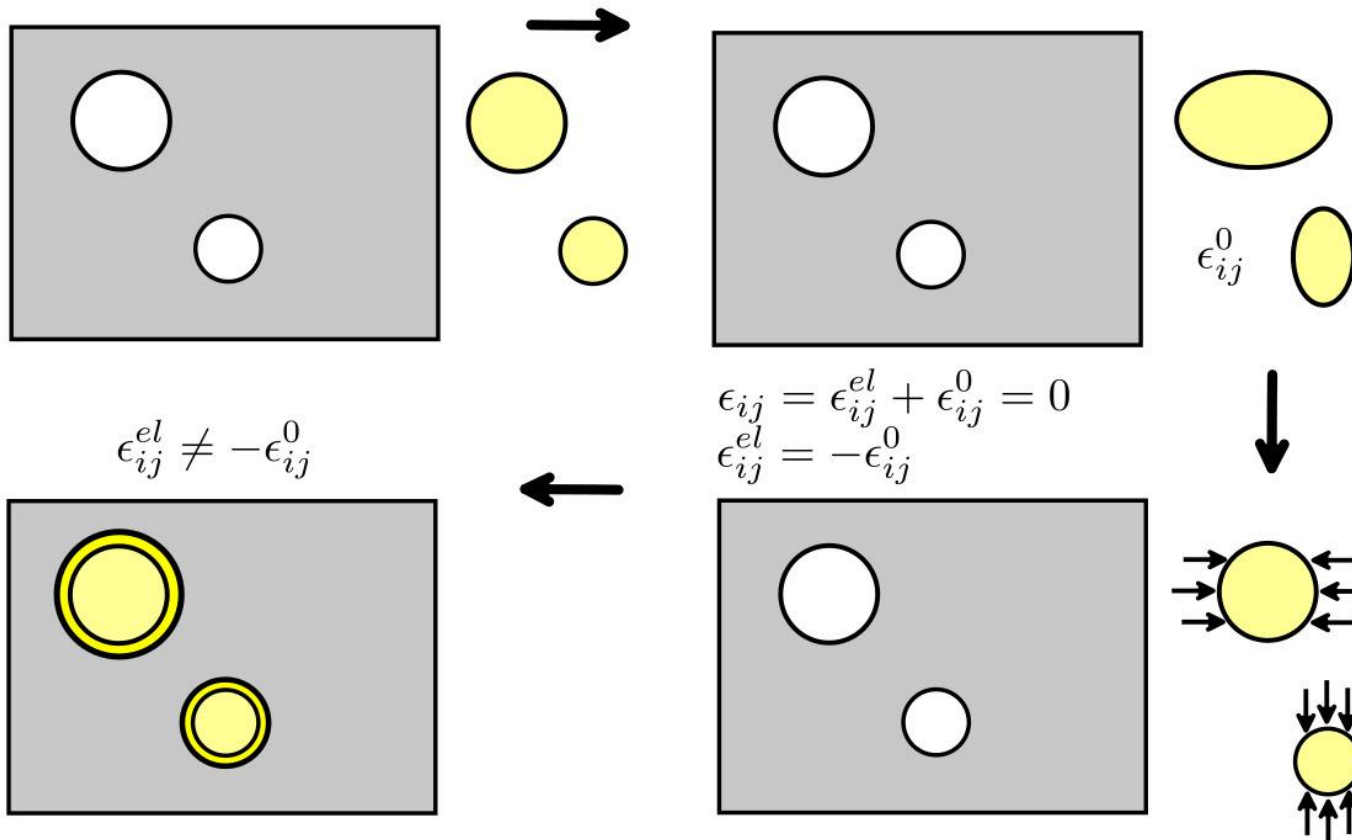
Stresses  $\rightarrow$   $\left\{ \begin{array}{l} \nabla_j \sigma_{ij} = 0 \\ \sigma_{ij} = C_{ijkl} (\epsilon_{kl} - \epsilon_{kl}^0) \end{array} \right.$

Total strain  $\rightarrow$   $(\epsilon_{kl} - \epsilon_{kl}^0)$

Eigen strain  $\rightarrow$   $\epsilon_{kl}^0$

Stiffness tensor  $\rightarrow$   $C_{ijkl}$

Elastic strain  $\rightarrow$   $(\epsilon_{kl} - \epsilon_{kl}^0)$



\*A. Khachaturyan, Theory of Structural Transformations in Solids, 1983.

# Phase Field Model

Excess quenched-in vacancies\* present in as built samples of L-PPF

Non-equilibrium  
vacancy site fraction

$$X_{Va}(t + dt) = X_{Va}(t) + \left[ 1 - \exp\left(-\frac{D_{Va}}{L_{Va}^2} dt\right) \right] [X_{Va}^e(T(t)) - X_{Va}(t)]$$

Mean vacancy  
diffusion path

Vacancy site fraction  
at equilibrium

Vacancy diffusion  
coefficient

Impurity diffusion  
coefficient of Si in Al

$$D_{Va} = \frac{X_{Va}}{X_{Va}^e} (X_{Si} * D_{Si}^{Al} + (1 - X_{Si}) * D_{Al}^{Al})$$

Molar fraction of Si

Self-diffusion  
coefficient of Al

# Phase Field Model

Vacancy diffusion coefficient  
Modified due to excess of  
vacancies \*

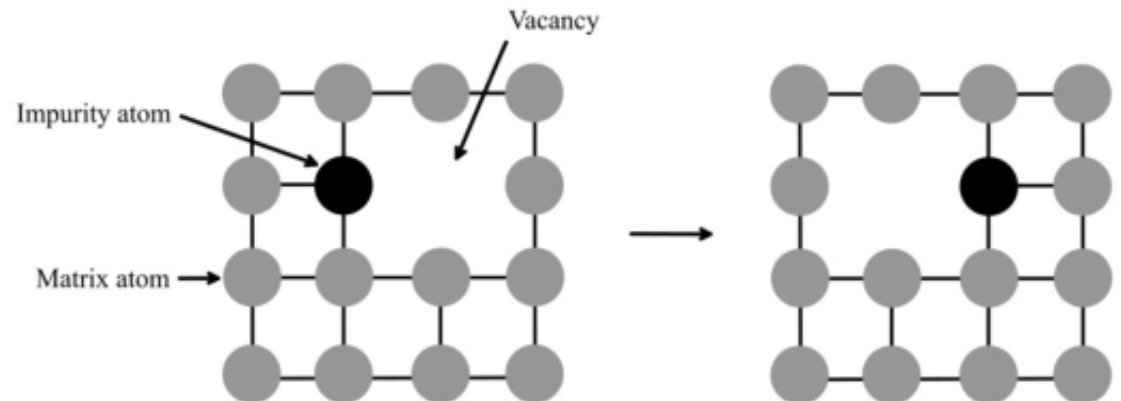
$$D_{Va} = \frac{X_{Va}}{X_{Va}^e} (X_{Si} {}^*D_{Si}^{Al} + (1 - X_{Si}) {}^*D_{Al}^{Al})$$

Modified impurity diffusion  
coefficient of Si in Al

Original impurity diffusion  
coefficient of Si in Al

$${}^*D_{Si}^{Al} = \left( \frac{X_{Va}}{X_{Va}^e} \right) {}^*D_{0Si}^{Al} \exp\left(-\frac{Q_{{}^*D_{Si}^{Al}}}{RT}\right)$$

Vacancy site fraction  
at equilibrium



# Phase Field Model

## Governing equations

- Cahn-Hilliard for conserved field (molar fraction of Si in Al)

$$\frac{\partial X_{Si}}{\partial t} = \nabla \cdot \left( \frac{\tilde{D}}{\partial^2 f_0 / \partial X_{Si}^2} \nabla \frac{\delta \mathcal{F}}{\delta X_{Si}} \right)$$

Al/Si Inter-diffusivity (points to  $\tilde{D}$ )  
Interface kinetic coefficient (points to  $L$ )

Homogeneous free energy (points to  $\partial^2 f_0 / \partial X_{Si}^2$ )  
Non homogeneous free energy (points to  $\delta \mathcal{F} / \delta X_{Si}$ )

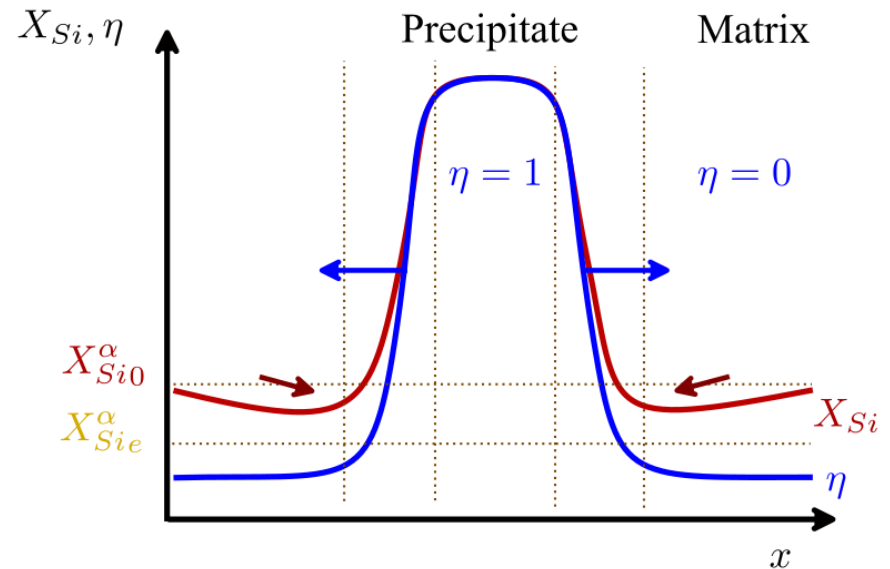
- Allen-Cahn for non-conserved field (phase)

Interface kinetic coefficient

$$\frac{\partial \eta}{\partial t} = -L \frac{\delta \mathcal{F}}{\delta \eta}$$

- Solved by Fourier spectral methods

Molar fraction of Si, Phase



Evolution between initial out-of-balance system 0 and equilibrium one e



# 1st validation: simulation of DSC curve

Heat flow rate absorbed / released by precipitate growth and coarsening

Heat flow rate

Volume

Molar mass

Molar enthalpy of phase  $\phi$

Phase variable

Molar fraction of  $i$

Coarsening heat or surface energy term

Heat capacity

Diffusion heat

Precipitation heat

$$\dot{q}_w = \frac{1}{V} \frac{d}{dt} \int_V \sum_{\phi} d(H_m^{\phi} \eta^{\phi}) u^{\phi} dV$$

$$d(H_m^{\phi} \eta^{\phi}) = \eta^{\phi} \left( C_p^{\phi} dT + \sum_i \frac{\partial H_m^{\phi}}{\partial X_i} dX_i \right) + H_m^{\phi} d\eta^{\phi} + \gamma_H dA$$

# Model parameters

Model parameter	Symbol	Simplification	Tool / experiment	Reference
Free energy density	$f^\alpha, f^d$	Parabola fitting	CALPHAD modeling	[ADR98]
Al/Si Inter-diffusivity	$\tilde{D}$	Al/Si Impurity diffusion coefficient		[Man+09]
Al Self-diffusivity	$*D_{Al}^{Al}$			[Man+09]
Interfacial mobility	$M_\eta$		DSC experiment	In-house experiment
Al/Si interface energy	$\gamma$		Back calculation from nucleation rate experiment	[RT58]
Initial conditions (phase fraction and molar fraction of Si)	$\eta^0, X_{Si}^0$		XRD + SEM analysis	In-house experiment
Molar volume	$V_m$		CALPHAD modeling	[Hal07]
Stiffness tensor	$C_{ijkl}$	Use Aluminum value for the whole system	CALPHAD modeling	[Su+15]
Equilibrium vacancy site fraction	$X_{Va}^e$			[Meh07]

[ADR98] I. Ansara, A.T. Dinsdale, M.H. Rand, COST 507 - Definition of Thermochemical and Thermophysical Properties to Provide a Database for the Development of New Light Alloys, 1998.

[Man+09] M. Mantina, Y. Wang, L.Q. Chen, Z.K. Liu, C. Wolverton, Acta Materialia 57 (2009) 4102–4108.

[Hal07] B. Hallstedt, Calphad 31 (2007) 292–302.

[RT58] H.. Rosenbaum, D. Turnbull, Acta Metallurgica 6 (1958) 653–659.

[Su+15] D. Su, Y.-L. He, J.-Q. Liu, X.-G. Lu, ICISMME, 2015.

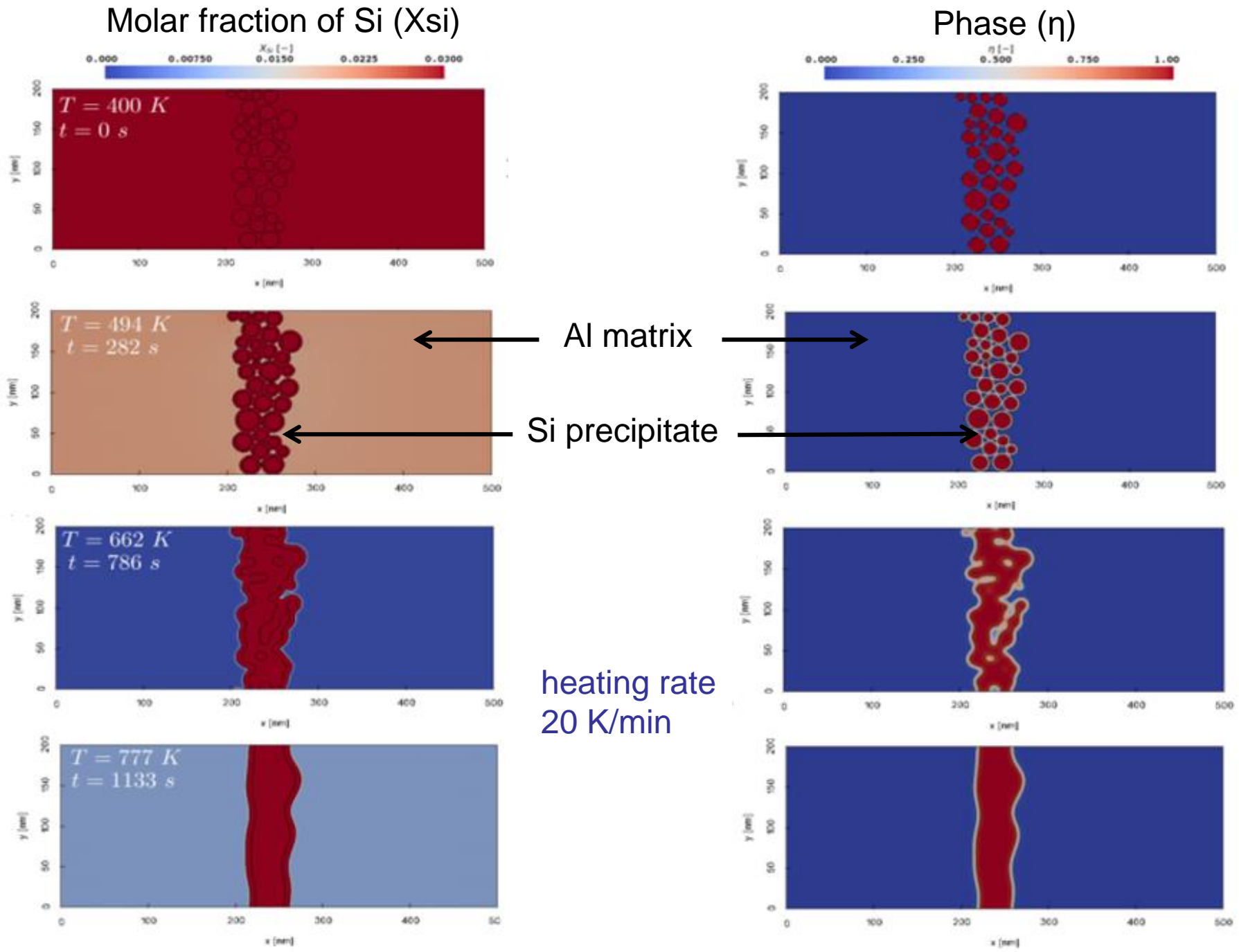
[Meh07] H. Mehrer, Diffusion in Solids: Fundamentals, Methods, Materials, Diffusion-Controlled Processes, Springer Science & Business Media, 2007.

# First simulation: sensitivity to L

## Interface kinetic coefficient

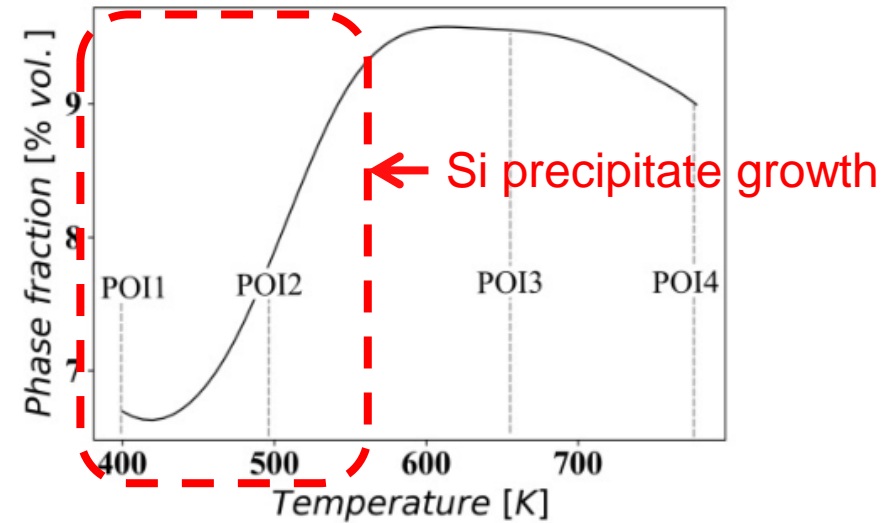
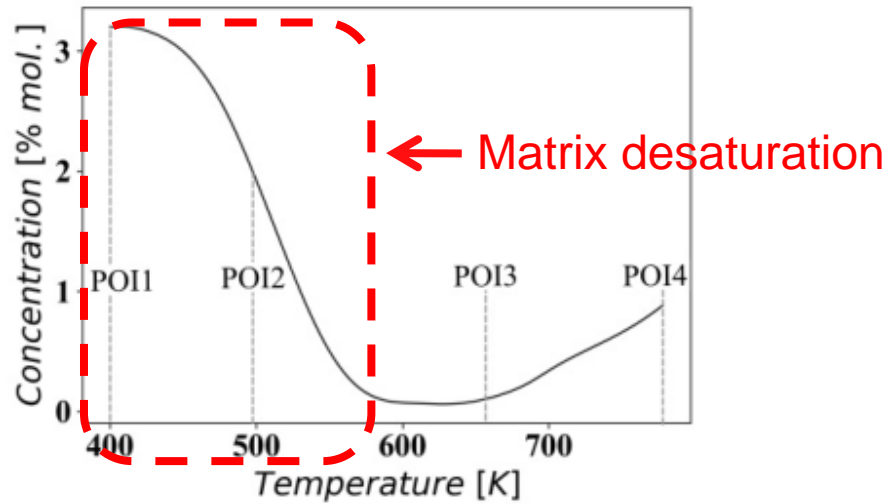
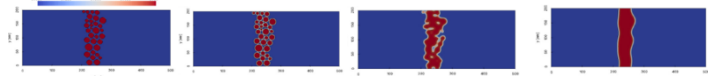
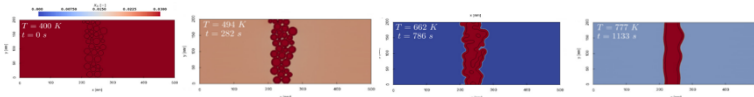
- Domain size 200x500 nm, grid size 1 nm
- Maximum value of the interface kinetic coefficient L with the temperature **to ensure stability**
- $L_{\max} = a \exp (bT)$  with  $a=3.63 \times 10^{-18}$  and  $b=0.025$
- Small value of L: microstructure evolution is interfacial-controlled with a low transformation kinetic.
- Large value of L: microstructure evolution is diffusion-controlled with a higher kinetic especially when the temperature is high.

# 2D simulation of a Si precipitate wall

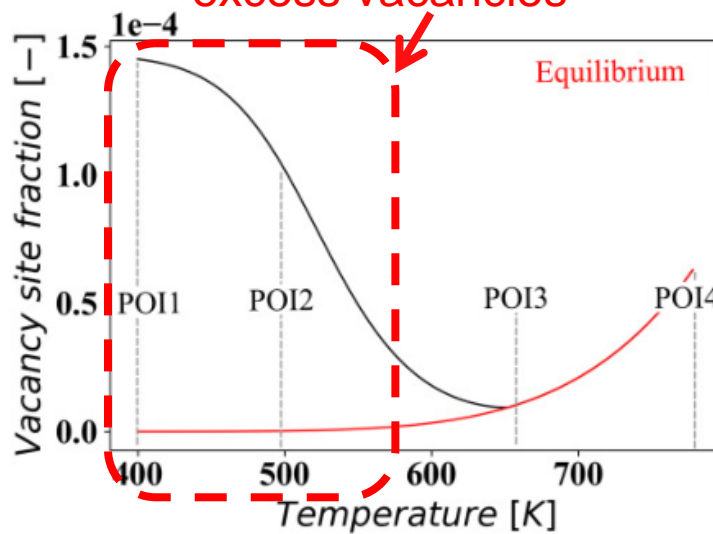


# 2D simulation of a Si precipitate wall

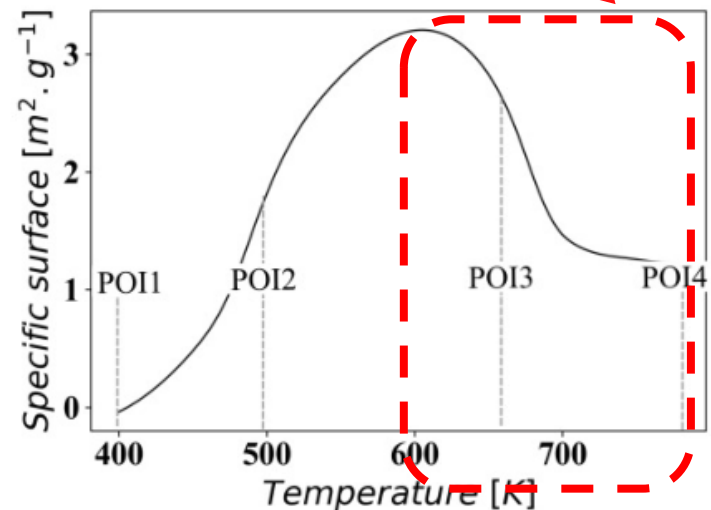
Evolution of average phase-field variables



Solute diffusion enhanced by excess vacancies



Si precipitate coalescence / coarsening

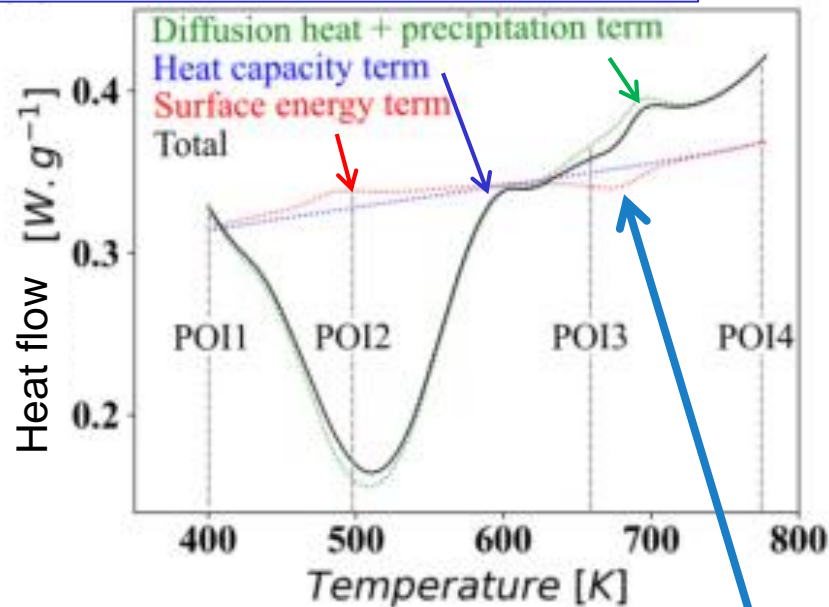


# 2D simulation of a Si precipitate wall

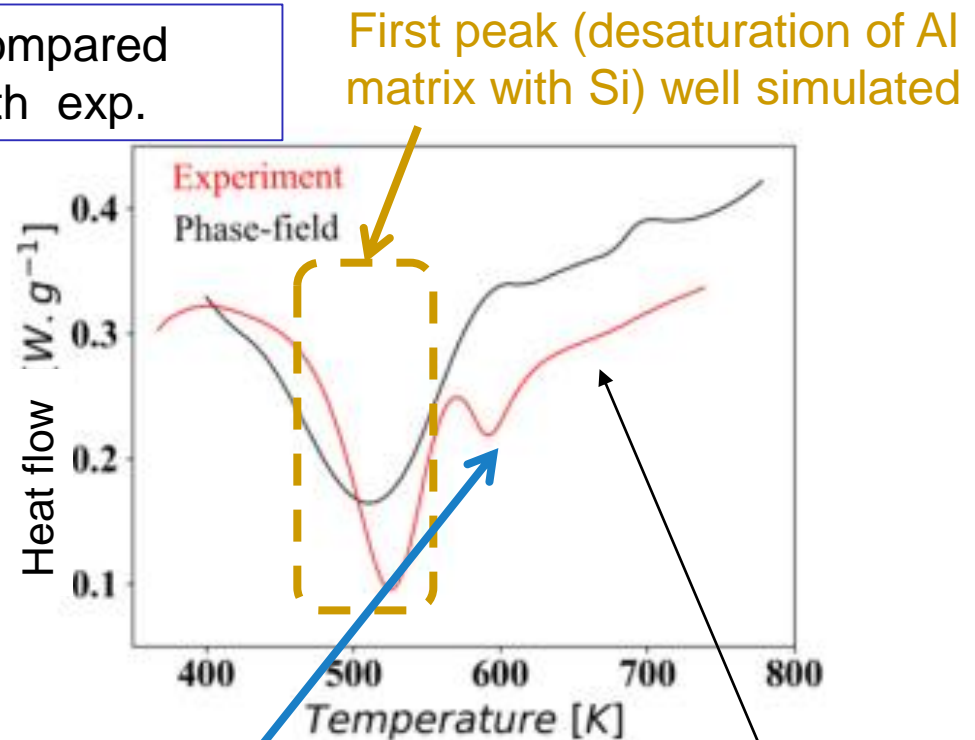
## Differential Scanning Calorimetry (DSC) prediction vs experiment

- Discrepancy with the baseline (heat capacity term) : heat peak area calibration  $\neq$  heat flow rate calibration for DSC device

Phase Field prediction



Compared with exp.

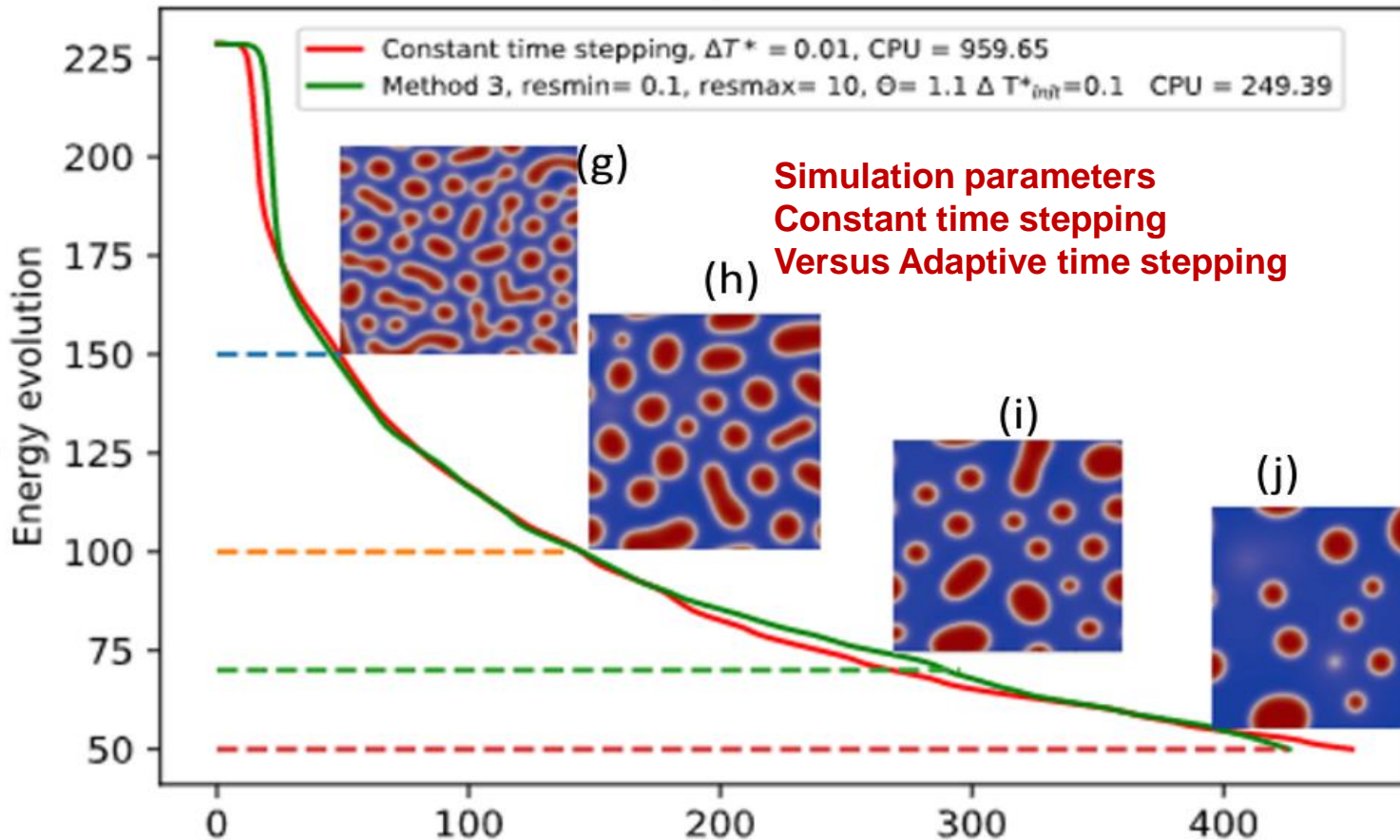


Second peak (Si precipitate coarsening) shifted to high temperature -> need to tune model parameters

Considering base line, experiment calibration not perfect so red line will  $\uparrow$

# Phase-Field simulations Adaptative time stepping

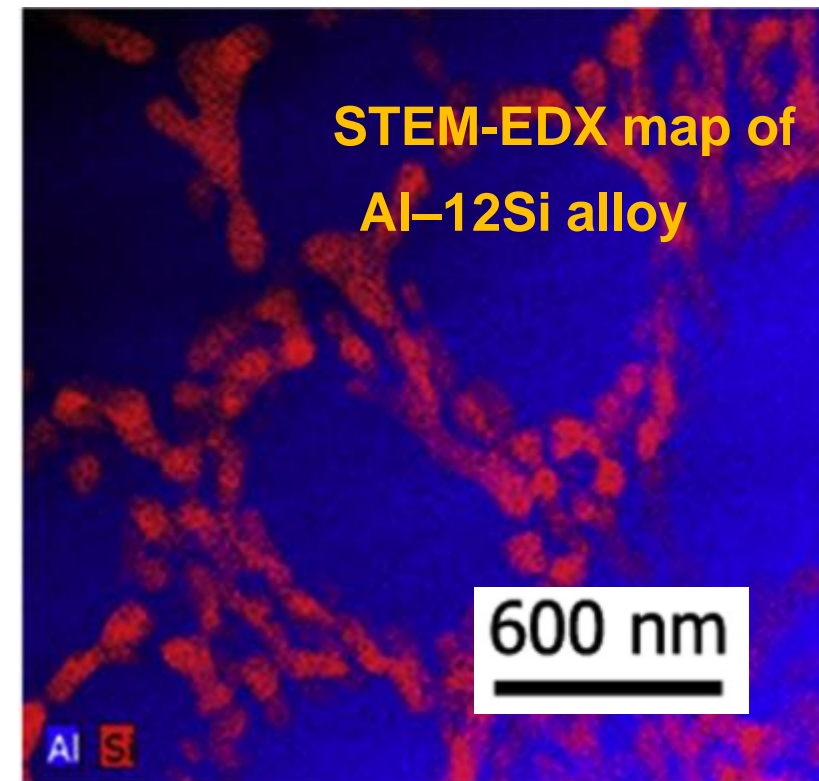
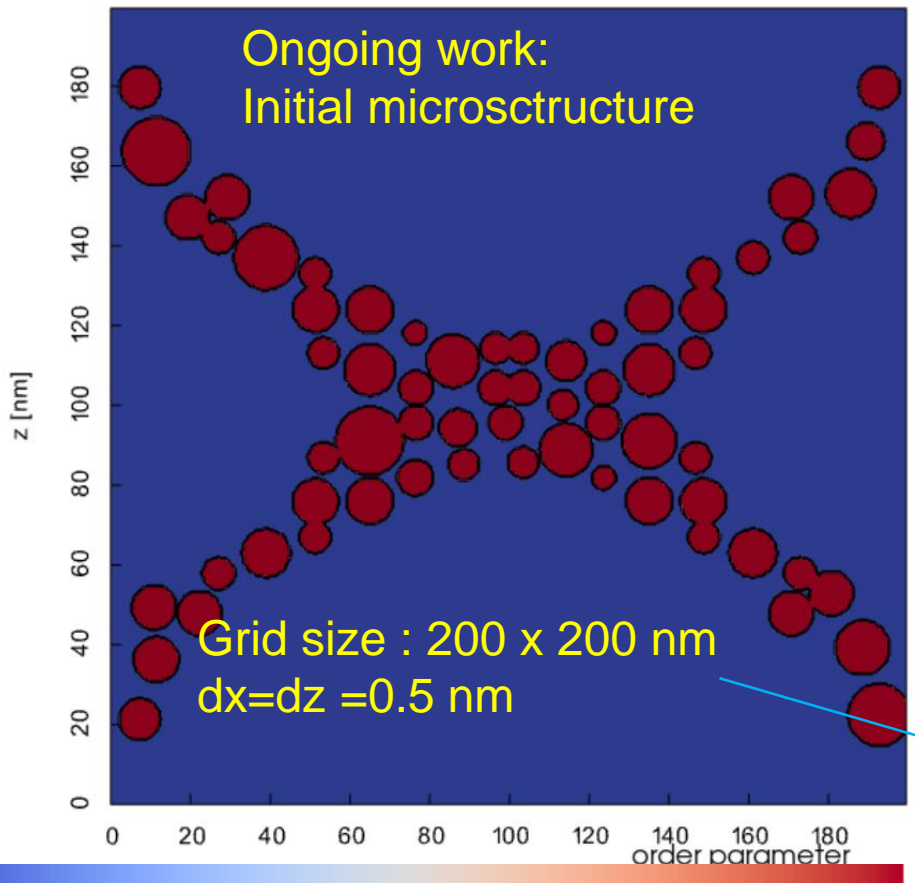
- To ensure and control the stability of the simulation.
- To speed up the simulation.



Solving  
Cahn Hilliard  
Conservative  
Equation

# 2D simulation DSC1<sup>st</sup> run (heating rate 20 K/min) evolution of Si precipitate wall

- no limitation on kinetic coefficient  $L$
- confirmation interface controlled microstructure evolution
- time step variable (3X smaller if evolutions occur)



X.P. Li et al., Acta Mater. **95** (2015), 74-82

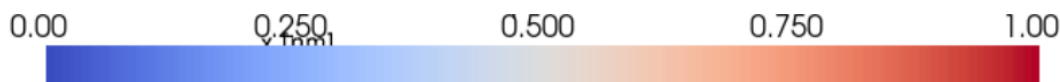
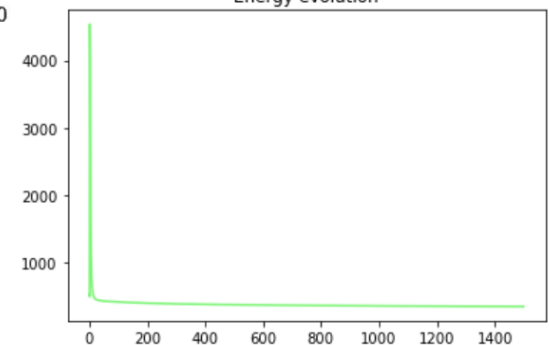
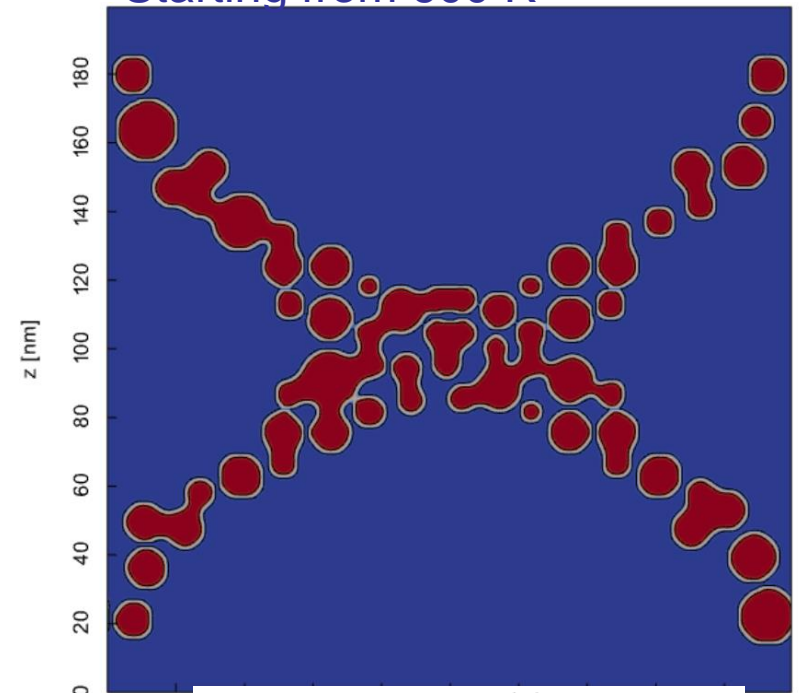
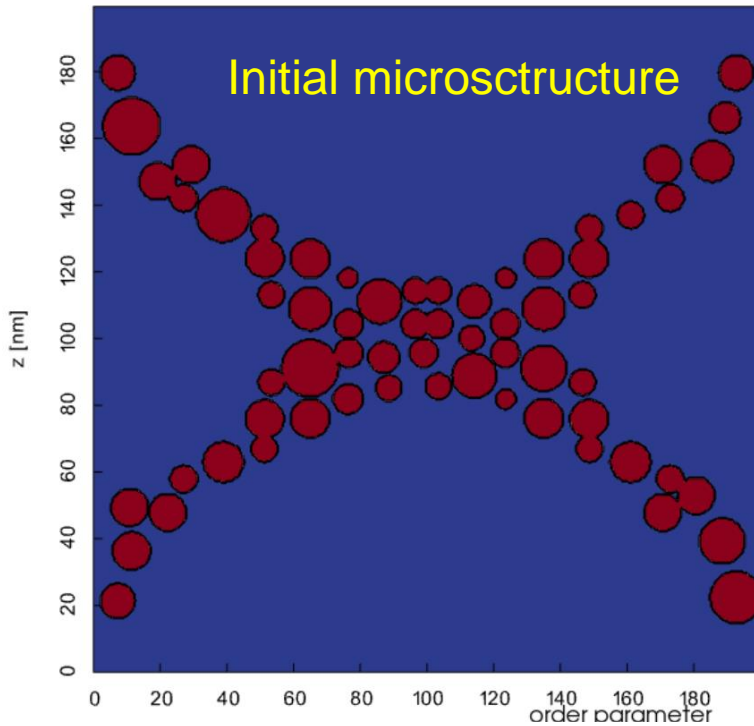
To increase to 500 x 500 nm (periodic cell)



# 2D simulation DSC1<sup>st</sup> run (heating rate 20 K/min) evolution of Si precipitate wall

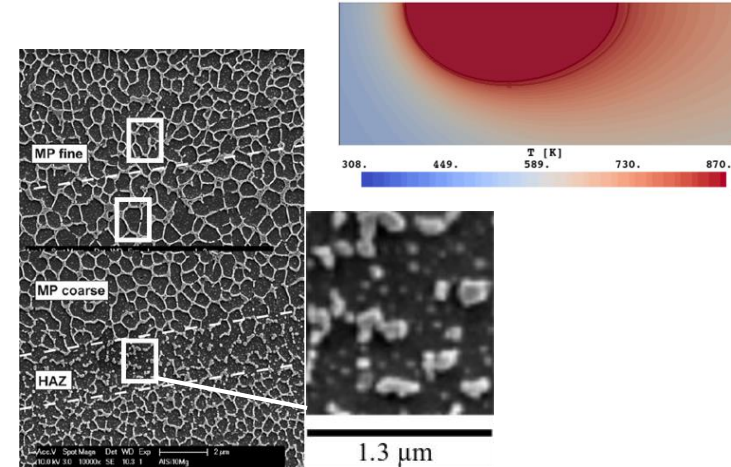
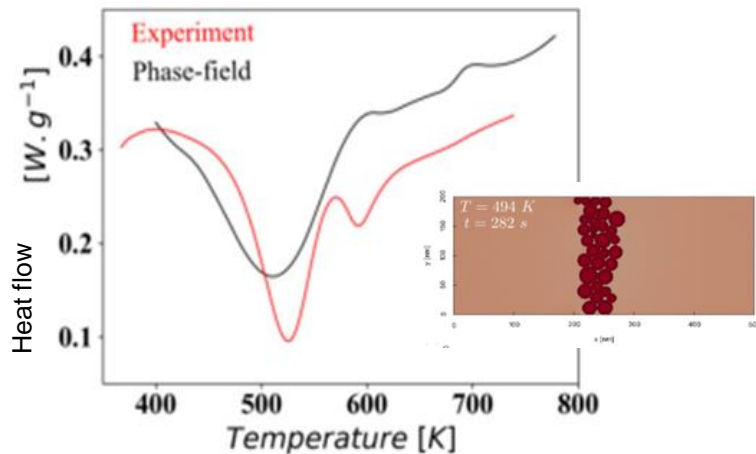
Simulation of a Representative wall of AlSi10Mg cell

Anisothermal heating (20 K/min)  
Starting from 600 K



# Conclusions - Phase Field

- KKS model + effect of excess quenched-in vacancies on Si solute diffusion
- Si precipitate growth and coarsening kinetics is predicted
- 1<sup>st</sup> simu agreement between predicted / experimental DSC curve Peak 1
- 2<sup>nd</sup> simu to predict Peak 2 related to Si precipitate coarsening

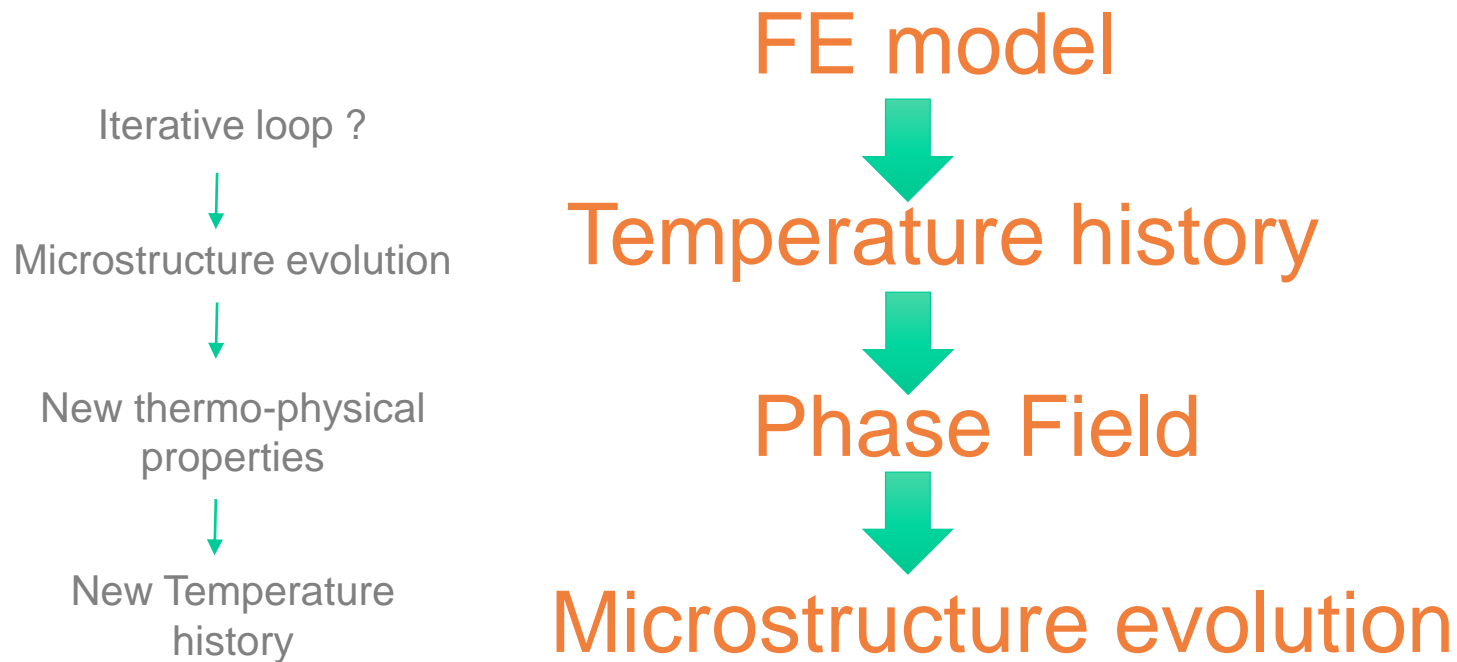


Transformation kinetics  
of bulk AlSi10Mg under a  
heating rate of 20 K/min  
(DSC conditions)



Transformation kinetics  
heating/cooling rate of 10<sup>6</sup> K/s  
(L-PBF conditions)

# Conclusions - Phase Field - FE



**Objective = microstructure prediction of As build L-PBF  
& As Built + heat treatments**

**Final Microstructure** → **Final Properties**